

## TO-92 Plastic-Encapsulate Transistors

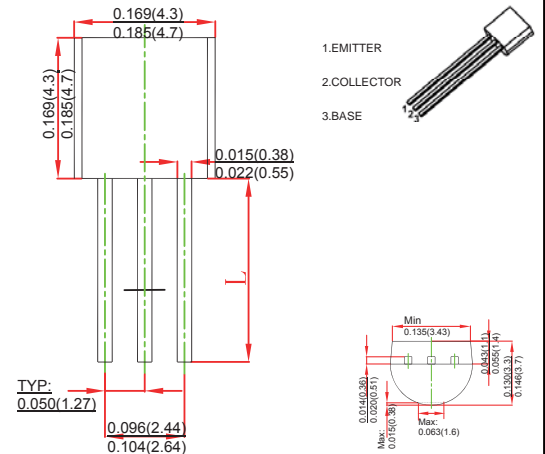
### FEATURES

- General Purpose Switching and Amplification.
- TRANSISTOR (NPN)

### MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any

### TO-92



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol Para	meter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	40	V
$V_{CEO}$	Collector-Emitter Voltage	25	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current	1.5	A
$P_C$	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	°C /W
$T_j$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55~+150	°C

## ELECTRICAL CHARACTERISTICS $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40\text{V}, I_E=0$			0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE}=20\text{V}, I_B=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	85		300	
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=800\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800\text{mA}, I_B=80\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800\text{mA}, I_B=80\text{mA}$			1.2	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$			1.0	V
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			15	pF
Transition frequency	$f_T$	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=30\text{MHz}$	100			MHz

### CLASSIFICATION OF $h_{FE(1)}$

RANK	BCD		
RANGE	85-160	120-200	160-300

# RATINGS AND CHARACTERISTIC CURVES

## Typical Characteristics

